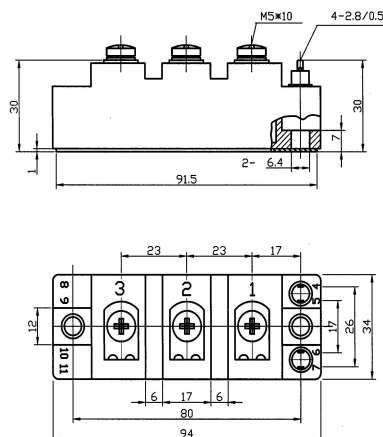
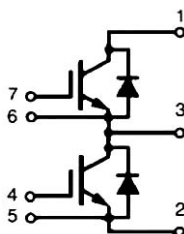


NPT IGBT Modules



$T_c = 25^{\circ}\text{C}$, unless otherwise specified

Symbol	Conditions	Values	Units
V _{CES}		1200	V
I _C	T _C = 25(80)°C	105(75)	A
I _{CRM}	T _C = 25(80)°C, t _P =1ms	210(150)	A
V _{GES}		±20	V
P _{tot}		625	W
T _{Vj} (T _{stg})	T _{OPERATION} ≤ T _{stg}	−40...+125(150)	°C
V _{isol}	AC, 1min	2500	V
R _{thJC}		≤ 0.2	K/W
R _{thJCD}		≤ 0.5	

SII75N12

NPT IGBT Modules

Electrical Characteristics

$T_c = 25^{\circ}\text{C}$, unless otherwise specified

Symbol	Conditions	min.	typ.	max.	Units
Static Characteristics					
V _{GE(th)}	V _{GE} = V _{CE} , I _C =3mA	4.5	5.5	6.5	V
I _{CES}	V _{GE} = 0; V _{CE} = 1200V; T _j = 25(125) ^o C		1(4.5)	1.5	mA
I _{GES}	V _{GE} = 20V, V _{CE} = 0			320	nA
V _{CE(sat)}	I _C =75A; V _{GE} = 15V; T _j = 25(125) ^o C; chip level		2.5(3.1)	3(3.7)	V
AC Characteristics					
C _{ies}	under following conditions V _{GE} = 0, V _{CE} = 25V, f = 1MHz		5.5		nF
C _{oes}			0.8		
C _{res}			0.3		
g _{fs}	V _{CE} =20V, I _C =75A	31			S
Switching Characteristics					
t _{d(on)}	V _{CC} = 600V, I _C = 75A		30	60	ns
t _r	R _{Gon} = R _{Goff} =15Ω, T _j = 125 ^o C		70	140	
t _{d(off)}	V _{GE} = ± 15V		450	600	
t _f			70	100	
FWD under following conditions:					
V _F	I _F = 75A, V _{GE} = 0V, T _j = 25(125) ^o C		2.3(1.8)	2.8	V
t _{rr}	I _F =75A, V _R =−600V, V _{GE} =0V, di/dt=−900A/us, T _j = 125 ^o C		0.125		us
Q _{rr}	I _F = 75A, V _{GE} = 0V, V _R = −600V di/dt=− 900A/us, T _j = 25(125) ^o C		3.2(12)		uC
Mechanical Data					
M _s	to heatsink M6	3		5	Nm
M _t	to terminals M5	2.5		5	Nm
w				160	g

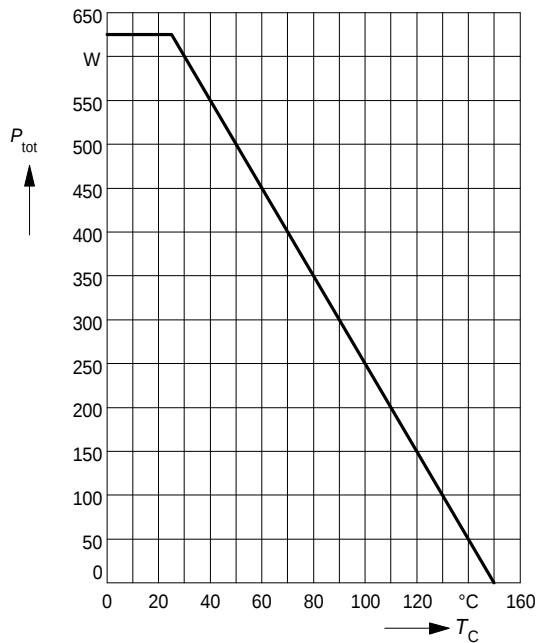
SII75N12

NPT IGBT Modules

Power dissipation

$$P_{\text{tot}} = f(T_C)$$

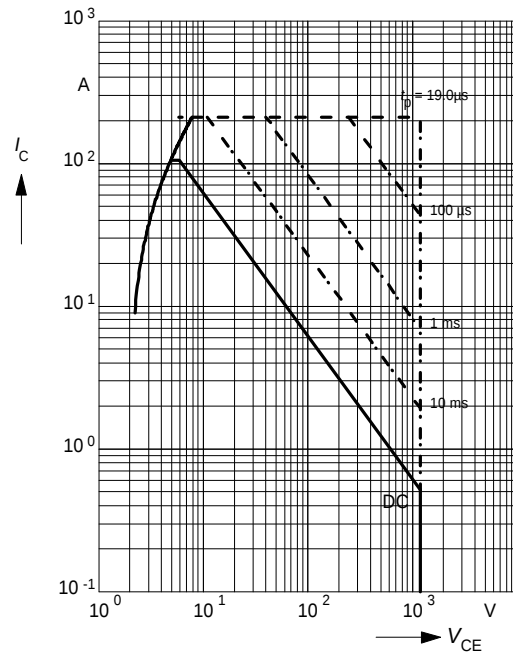
parameter: $T_j \leq 150^\circ\text{C}$



Safe operating area

$$I_C = f(V_{CE})$$

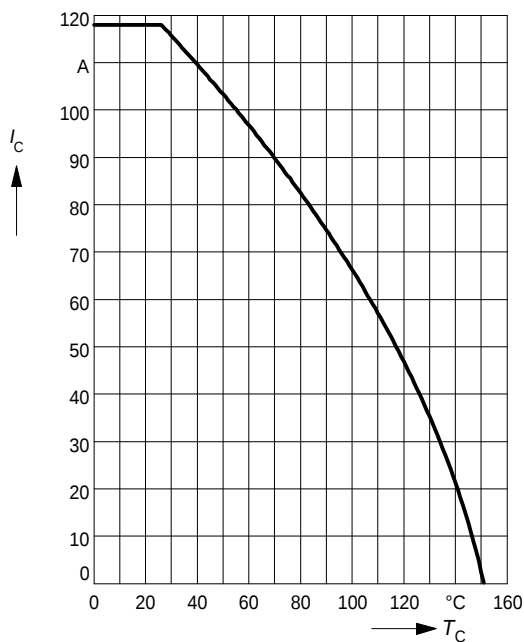
parameter: $D = 0$, $T_C = 25^\circ\text{C}$, $T_j \leq 150^\circ\text{C}$



Collector current

$$I_C = f(T_C)$$

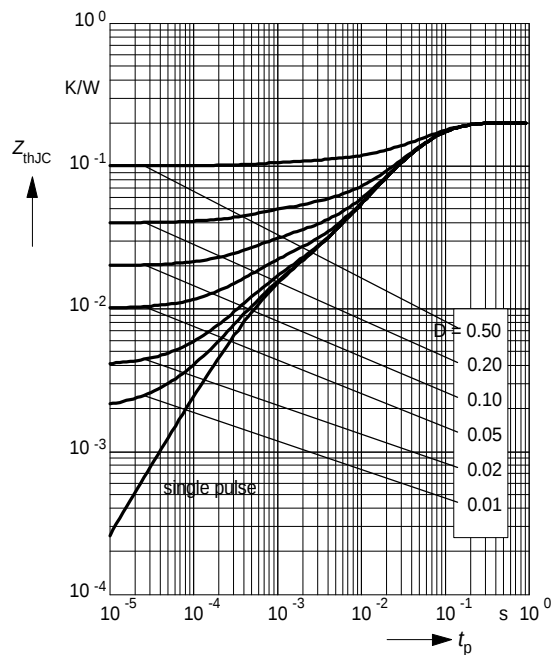
parameter: $V_{GE} \geq 15\text{ V}$, $T_j \leq 150^\circ\text{C}$



Transient thermal impedance IGBT

$$Z_{\text{thJC}} = f(t_p)$$

parameter: $D = t_p / T$



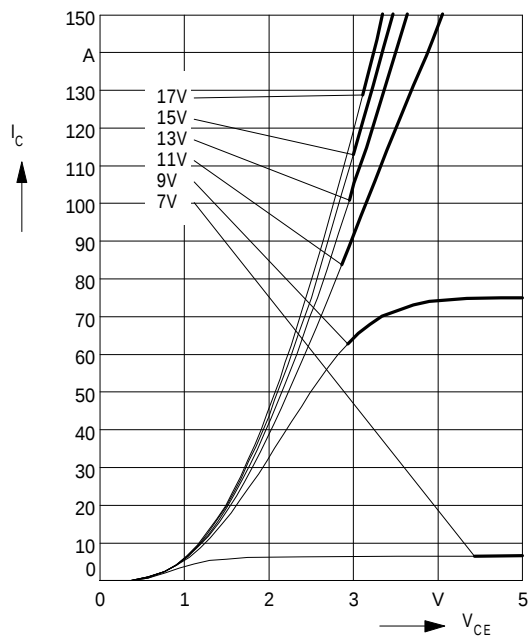
SII75N12

NPT IGBT Modules

Typ. output characteristics

$$I_C = f(V_{CE})$$

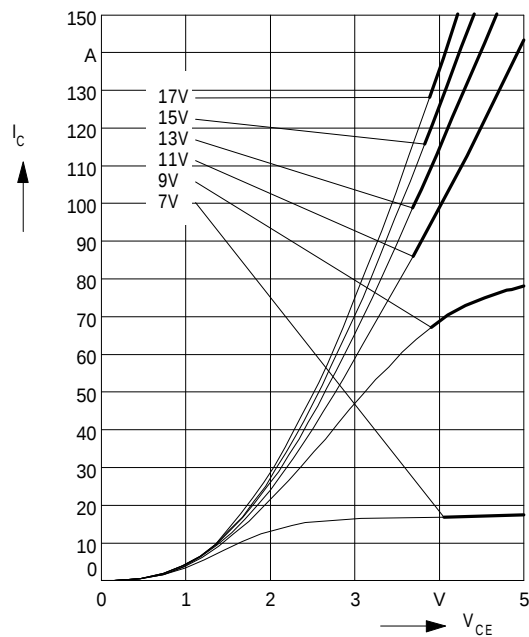
parameter: $t_p = 80 \mu s$, $T_j = 25^\circ C$



Typ. output characteristics

$$I_C = f(V_{CE})$$

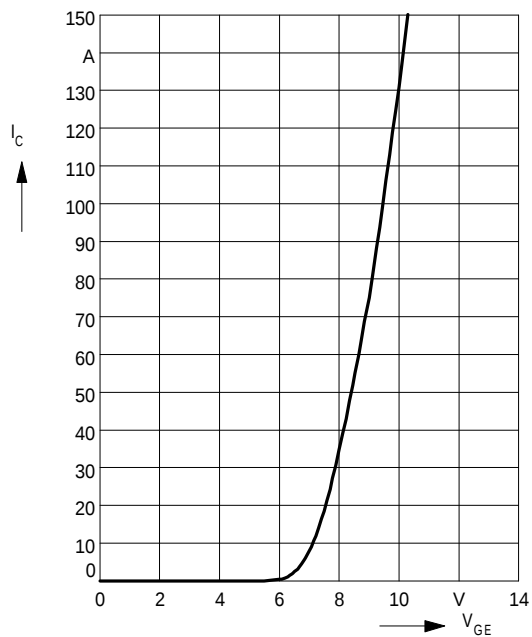
parameter: $t_p = 80 \mu s$, $T_j = 125^\circ C$



Typ. transfer characteristics

$$I_C = f(V_{GE})$$

parameter: $t_p = 80 \mu s$, $V_{CE} = 20 V$



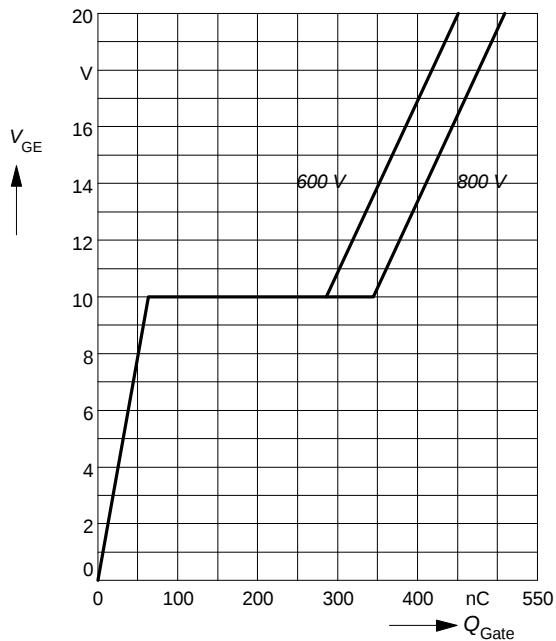
SII75N12

NPT IGBT Modules

Typ. gate charge

$$V_{GE} = f(Q_{Gate})$$

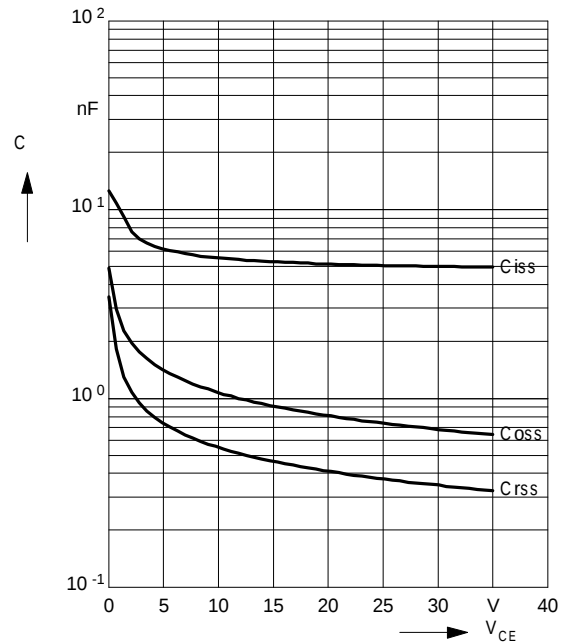
parameter: $I_{C\ puls} = 75\ A$



Typ. capacitances

$$C = f(V_{CE})$$

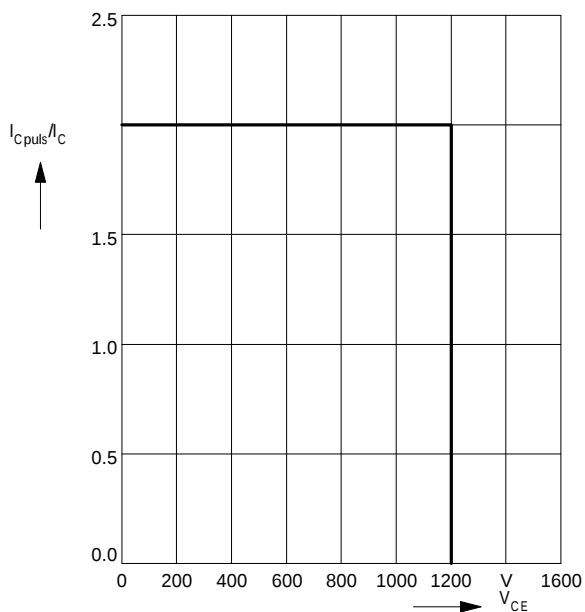
parameter: $V_{GE} = 0, f = 1\ MHz$



Reverse biased safe operating area

$$I_{C\ puls} = f(V_{CE}), T_j = 150^\circ C$$

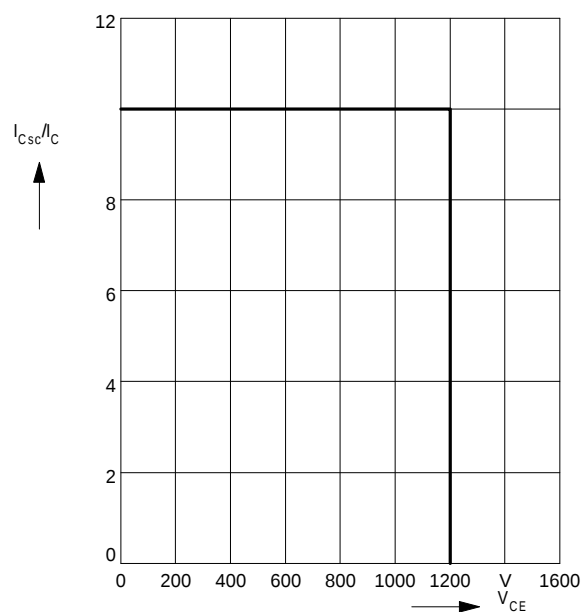
parameter: $V_{GE} = 15\ V$



Short circuit safe operating area

$$I_{C\ sc} = f(V_{CE}), T_j = 150^\circ C$$

parameter: $V_{GE} = \pm 15\ V, t_{sc} \leq 10\ \mu s, L < 50\ nH$



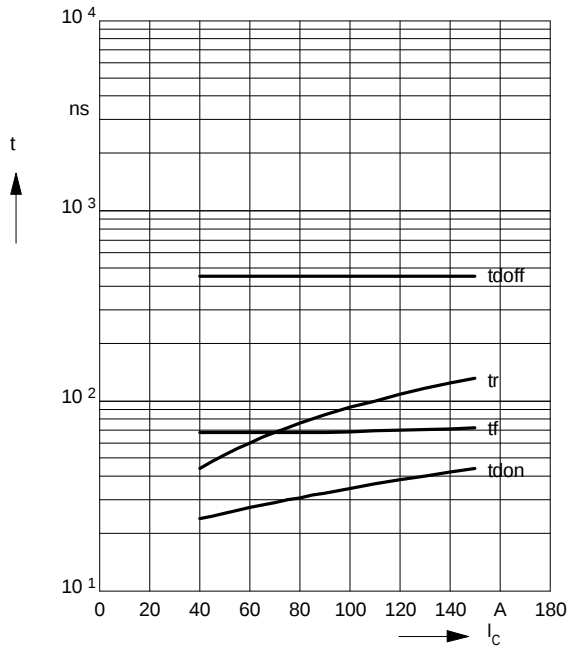
SII75N12

NPT IGBT Modules

Typ. switching time

$t = f(I_C)$, inductive load, $T_j = 125^\circ\text{C}$

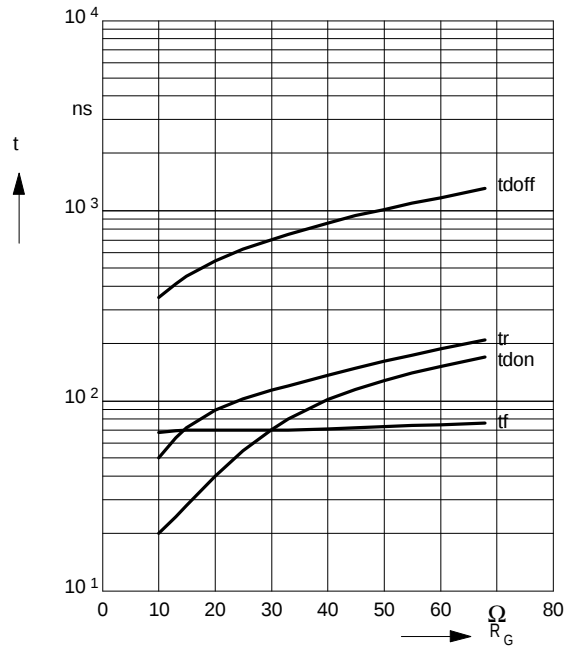
par.: $V_{CE} = 600\text{ V}$, $V_{GE} = \pm 15\text{ V}$, $R_G = 15\ \Omega$



Typ. switching time

$t = f(R_G)$, inductive load, $T_j = 125^\circ\text{C}$

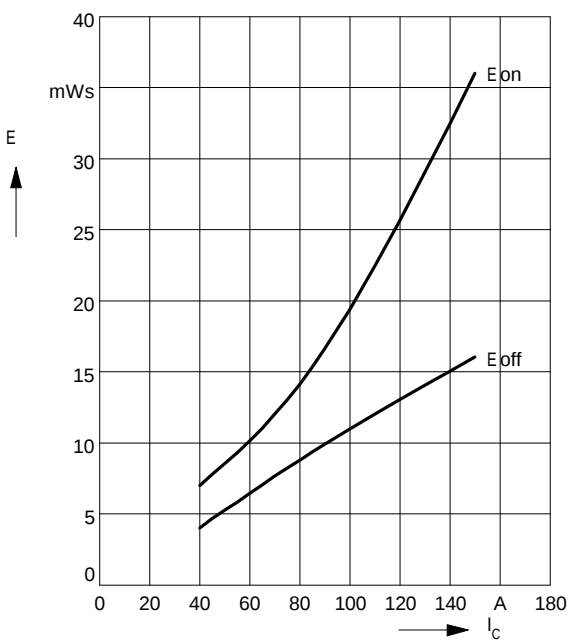
par.: $V_{CE} = 600\text{ V}$, $I_C = 75\text{ A}$



Typ. switching losses

$E = f(I_C)$, inductive load, $T_j = 125^\circ\text{C}$

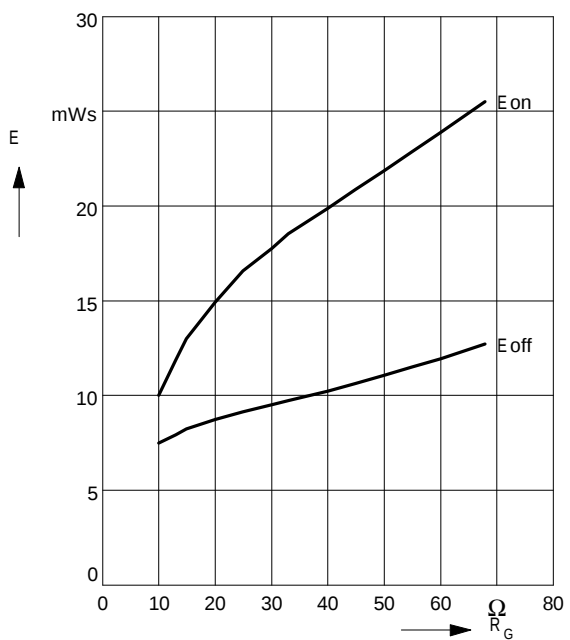
par.: $V_{CE} = 600\text{ V}$, $V_{GE} = \pm 15\text{ V}$, $R_G = 15\ \Omega$



Typ. switching losses

$E = f(R_G)$, inductive load, $T_j = 125^\circ\text{C}$

par.: $V_{CE} = 600\text{ V}$, $V_{GE} = \pm 15\text{ V}$, $I_C = 75\text{ A}$

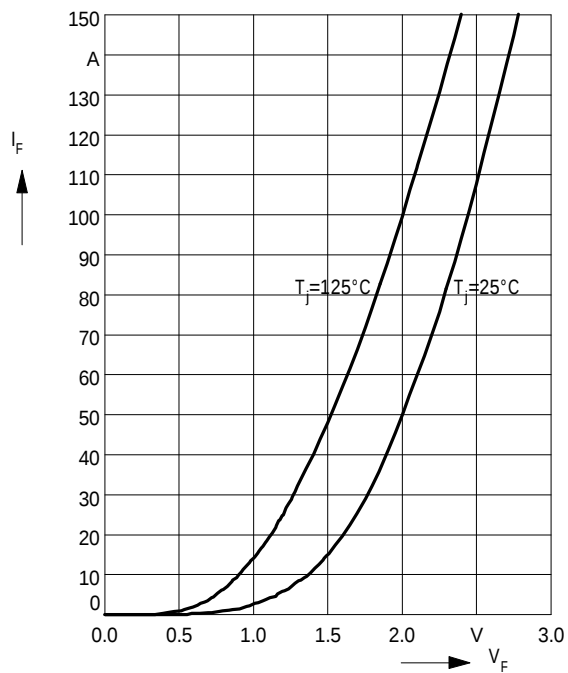


SII75N12

NPT IGBT Modules

Forward characteristics of fast recovery
reverse diode $I_F = f(V_F)$

parameter: T_j



Transient thermal impedance Diode

$$Z_{thJC} = f(t_p)$$

parameter: $D = t_p / T$

